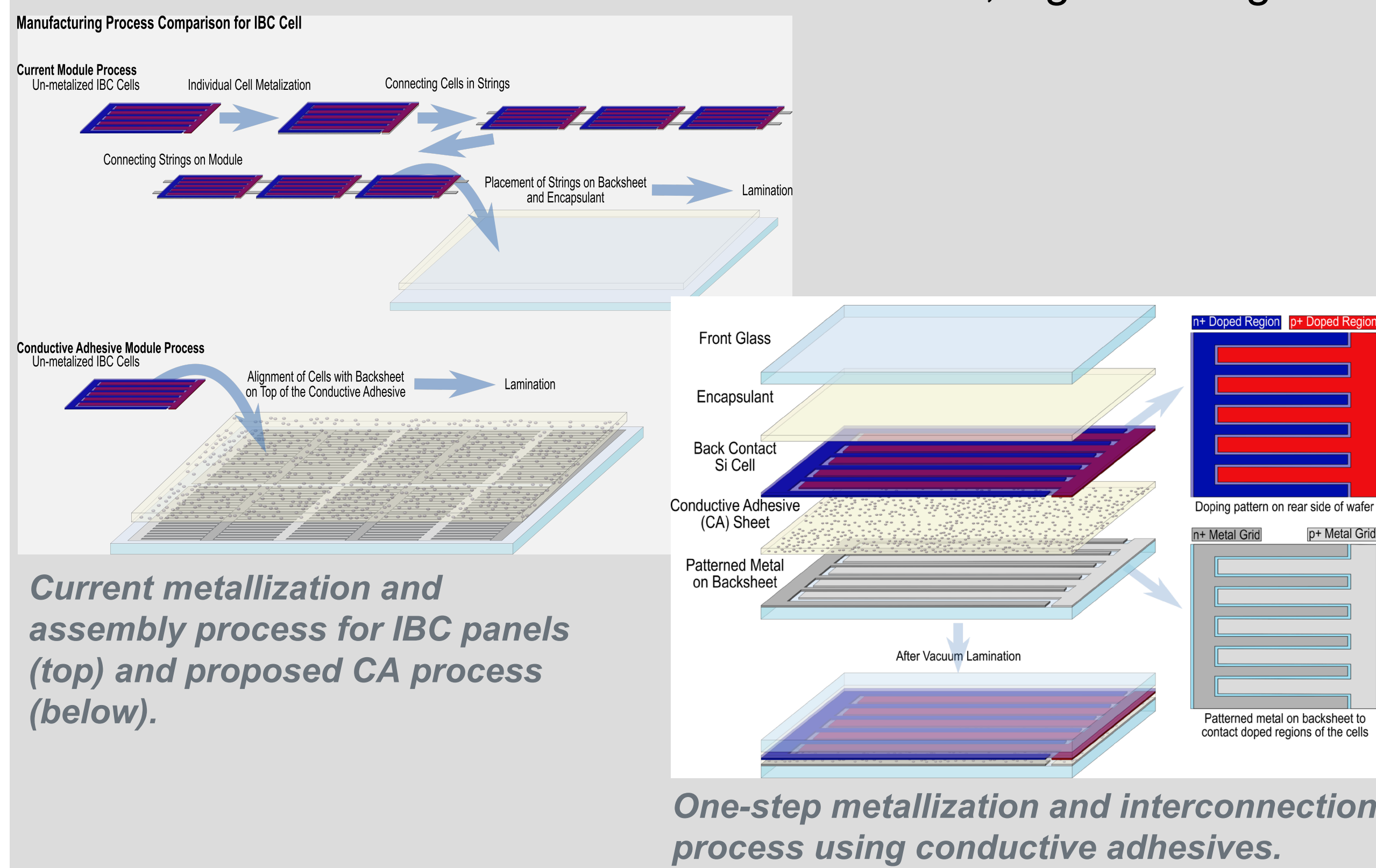




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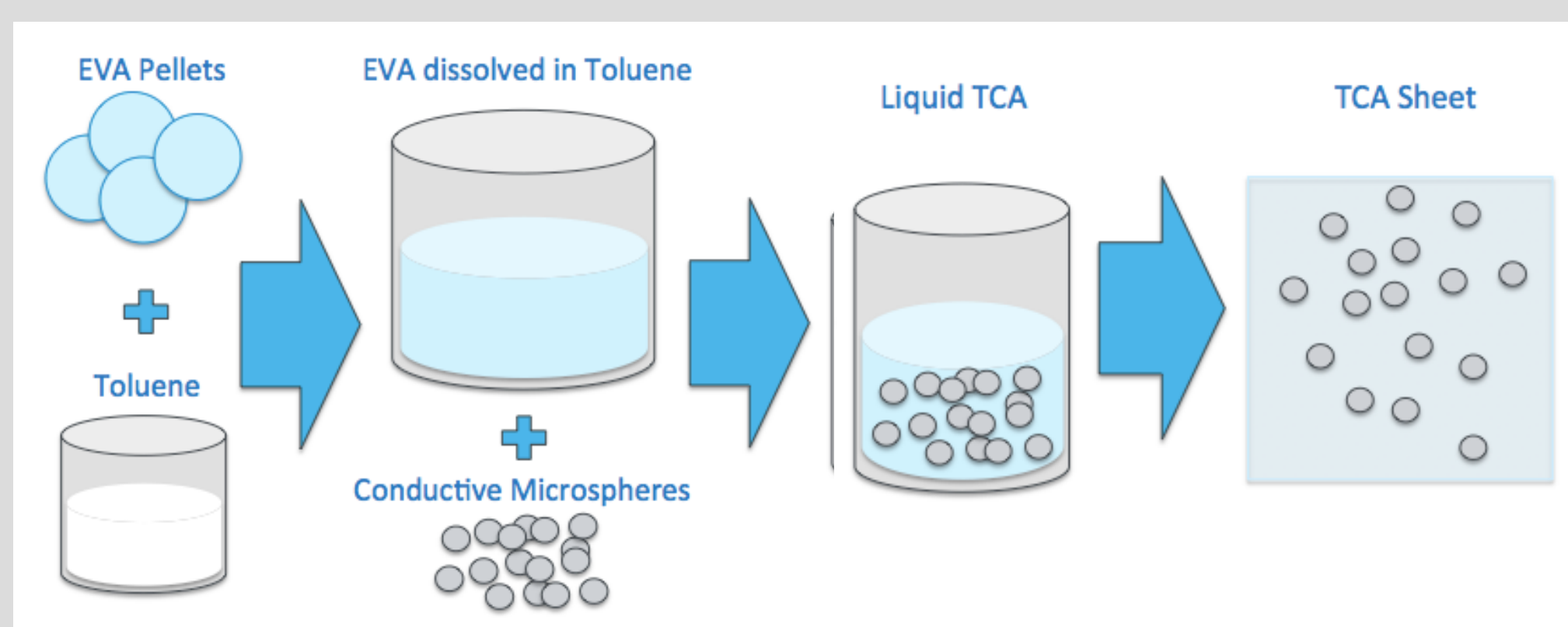
Background

- Metallization and assembly process for IBC panels requires multiple steps and a lot of silver:
 - Screen printing
 - Soldering into strings
 - Lay-up on back sheet & lamination
- Conductive adhesives (CA) would use a one-step metallization and interconnection process that combines with encapsulation using little silver for lower cost.
- No direct metallization of Si → fewer defects, higher voltage.

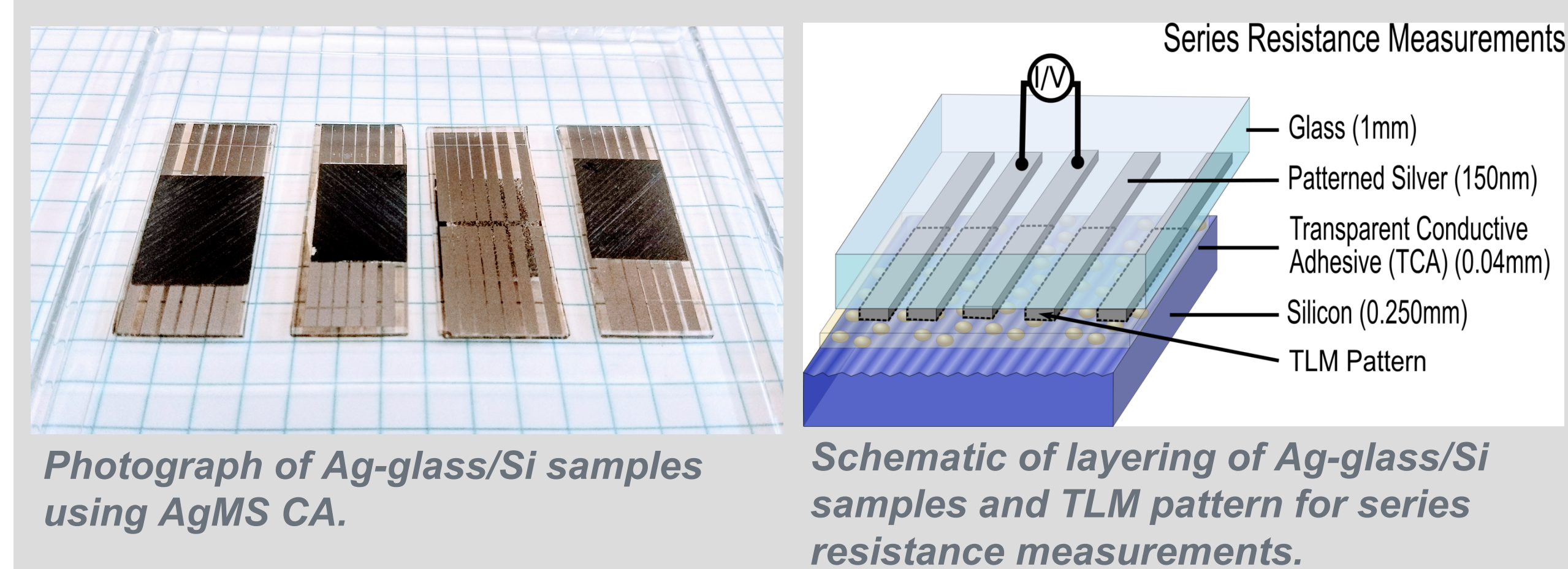


Methods

- Ethyl vinyl acetate (EVA) pellets mixed with toluene (in a 1:3 ratio) for 5 hours on hot plate at 120°C.
- EVA/toluene then used to make CA with silver-coated Poly(Methyl Methacrylate) Microspheres (AgMS) or 325 mesh indium powder.
- The CA mixture is used to produce a 300µm sheet using a universal applicator.
- Pieces of CA sheet are cut and hot pressed between a piece of glass with coplanar Ag electrodes (Ag-glass) and an HF-dipped Si wafer with a highly phosphorous-doped polysilicon surface.

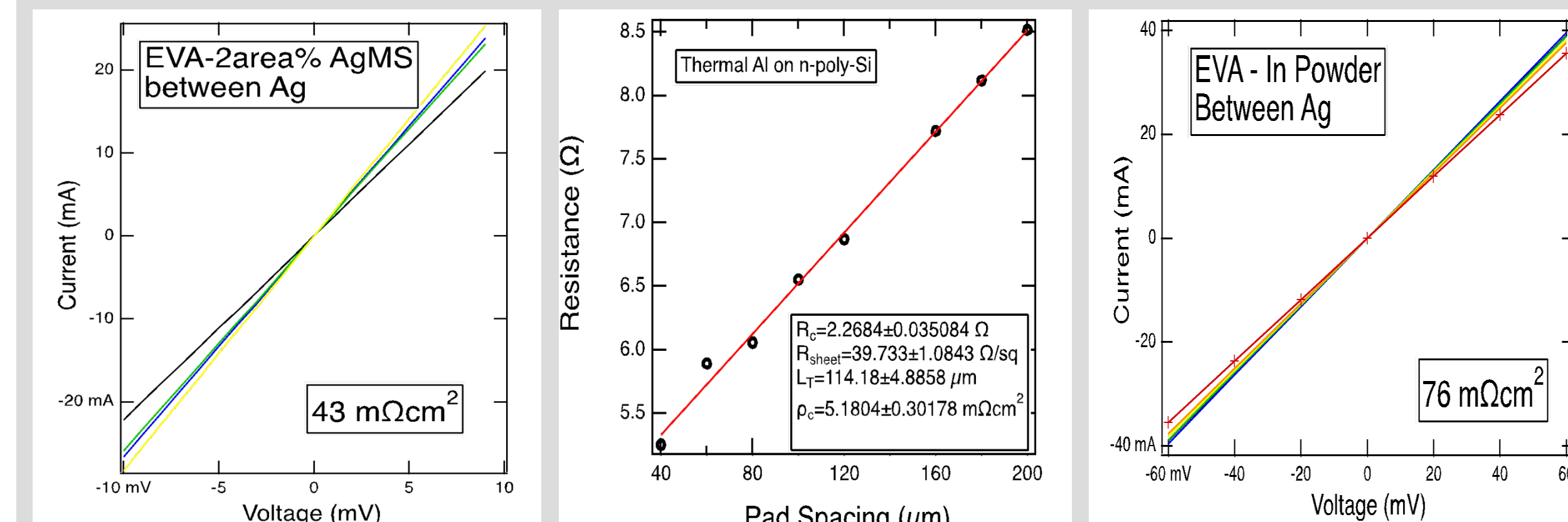


Schematic of CA sheet making process.



Reference Experiments

- Tested the different components of samples before combining CA and Si.
- Data shows EVA/AgMS and In-based CA should work.

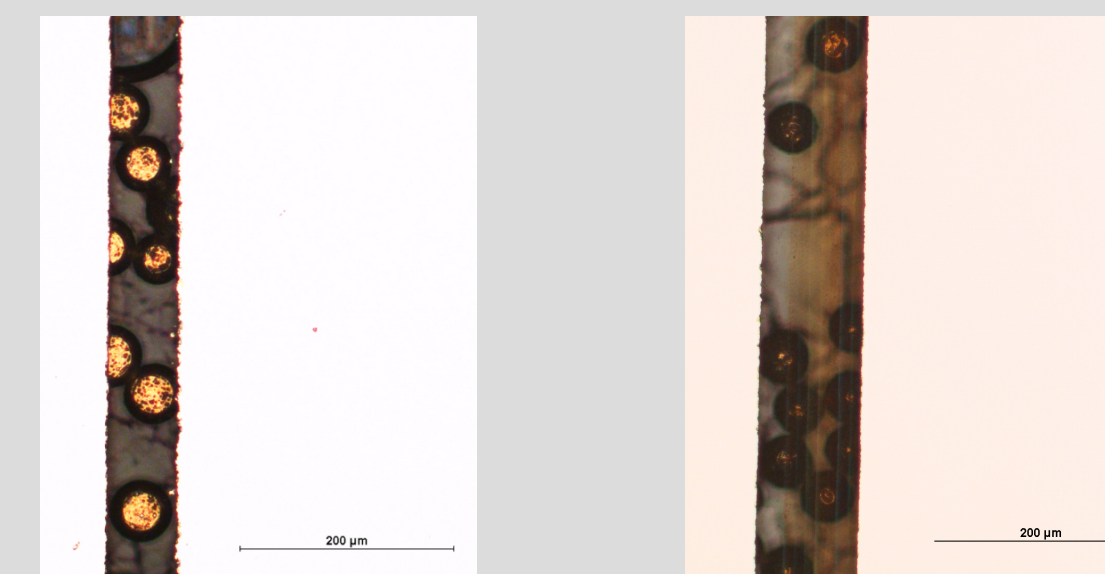


EVA/AgMS between Ag indicates that EVA/AgMS alone is conductive. **Si used lends itself to a decrease in contact resistivity.** **EVA/In between Ag indicates that EVA/In alone is conductive.**

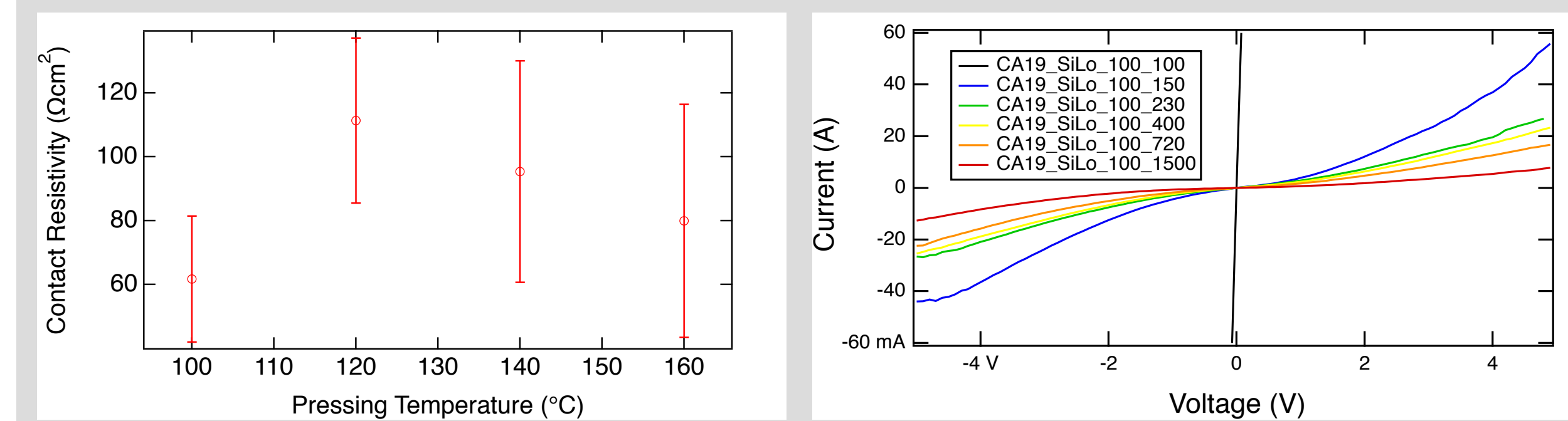
- Used Ag-glass/glass samples to test 5, 10, 15, and 20wt% CA.
 - Selected 10wt%, which is highest wt% without too many shunts (gap sizes: 100µm, 150µm, 230µm, 400µm, 720µm, and 1500µm).
- | Weight % AgMS | Smallest gap without shunt (µm) |
|---------------|---------------------------------|
| 5 | 150 |
| 10 | 230 |
| 15 | 400 |
| 20 | 400 |
- 5wt% yielded too little coverage while 15 and 20wt% yielded too much causing shunts.

EVA with AgMS Filler

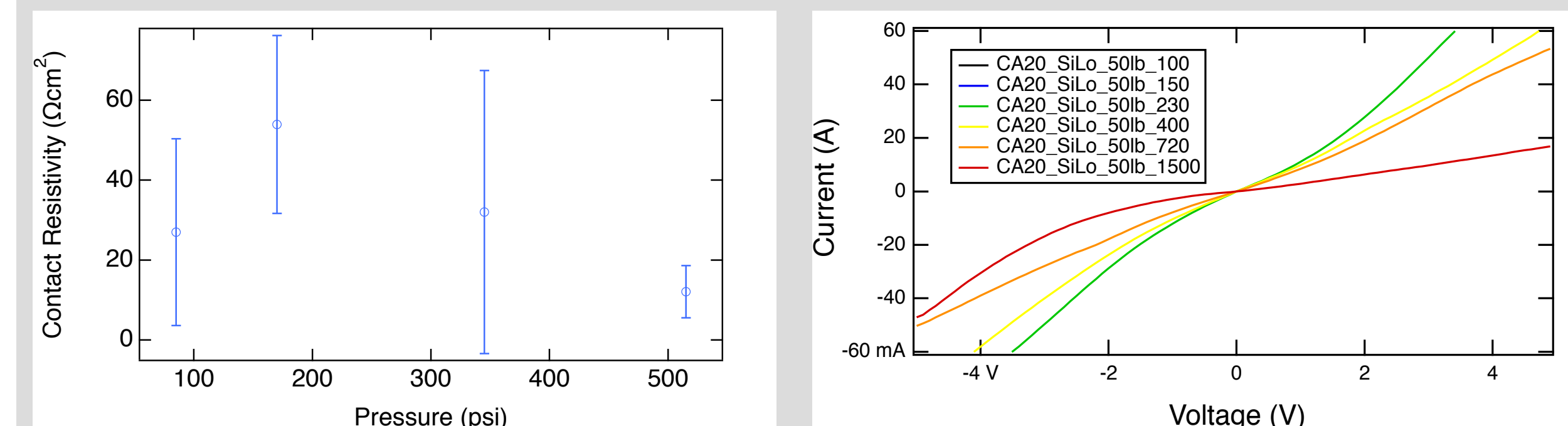
- Repeatedly getting ~20 Ωcm² with baseline experiment.
- Pressure series shows optically that 190 psi for 10 min. at 120°C is enough to produce good contact with microspheres.
- AgMS electrical data not ohmic and varies across samples after optimizing temperature and pressure.



Optical micrograph shows reflective spheres suggesting good contact. **Spheres not as reflective indicating bad contact.**



Mean contact resistivity as a function of temperature. **EVA/AgMS IV from temperature series.**

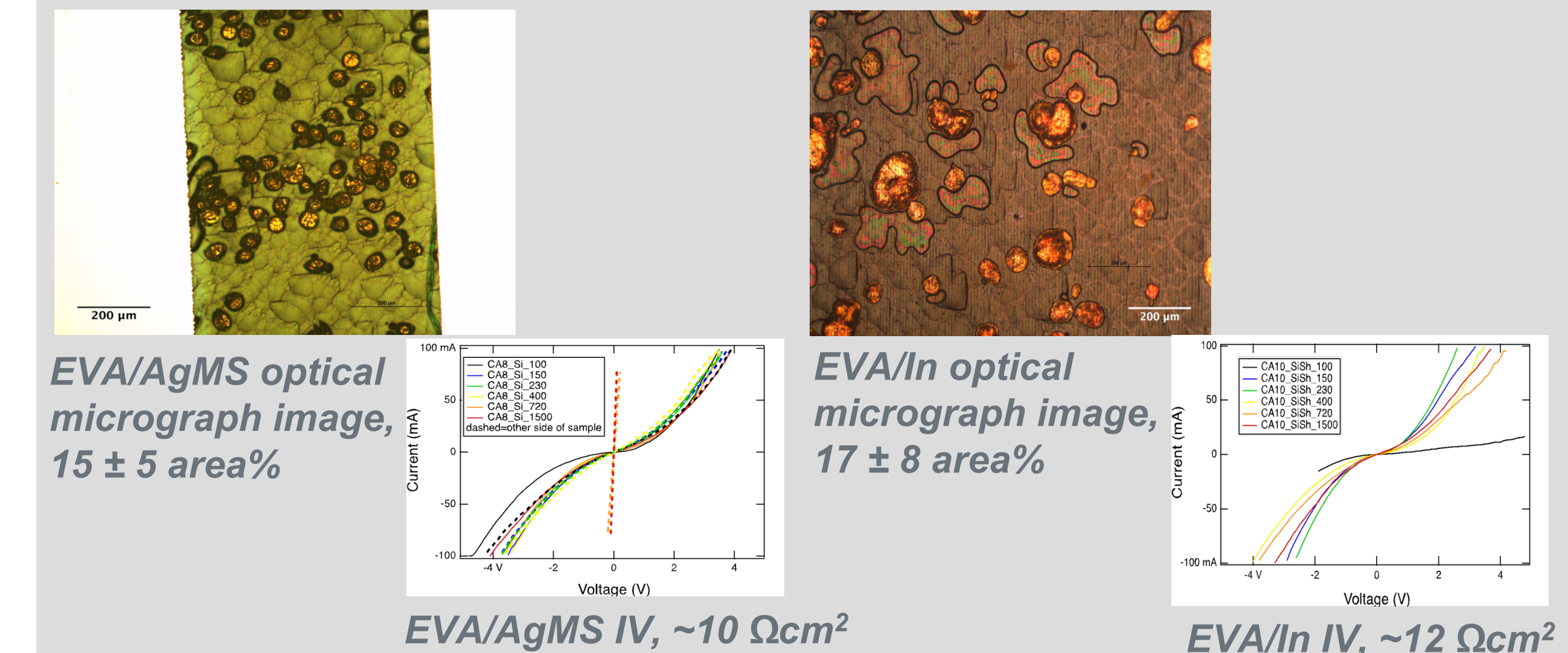


Mean contact resistivity as a function of pressure. **EVA/AgMS IV from pressure series.**

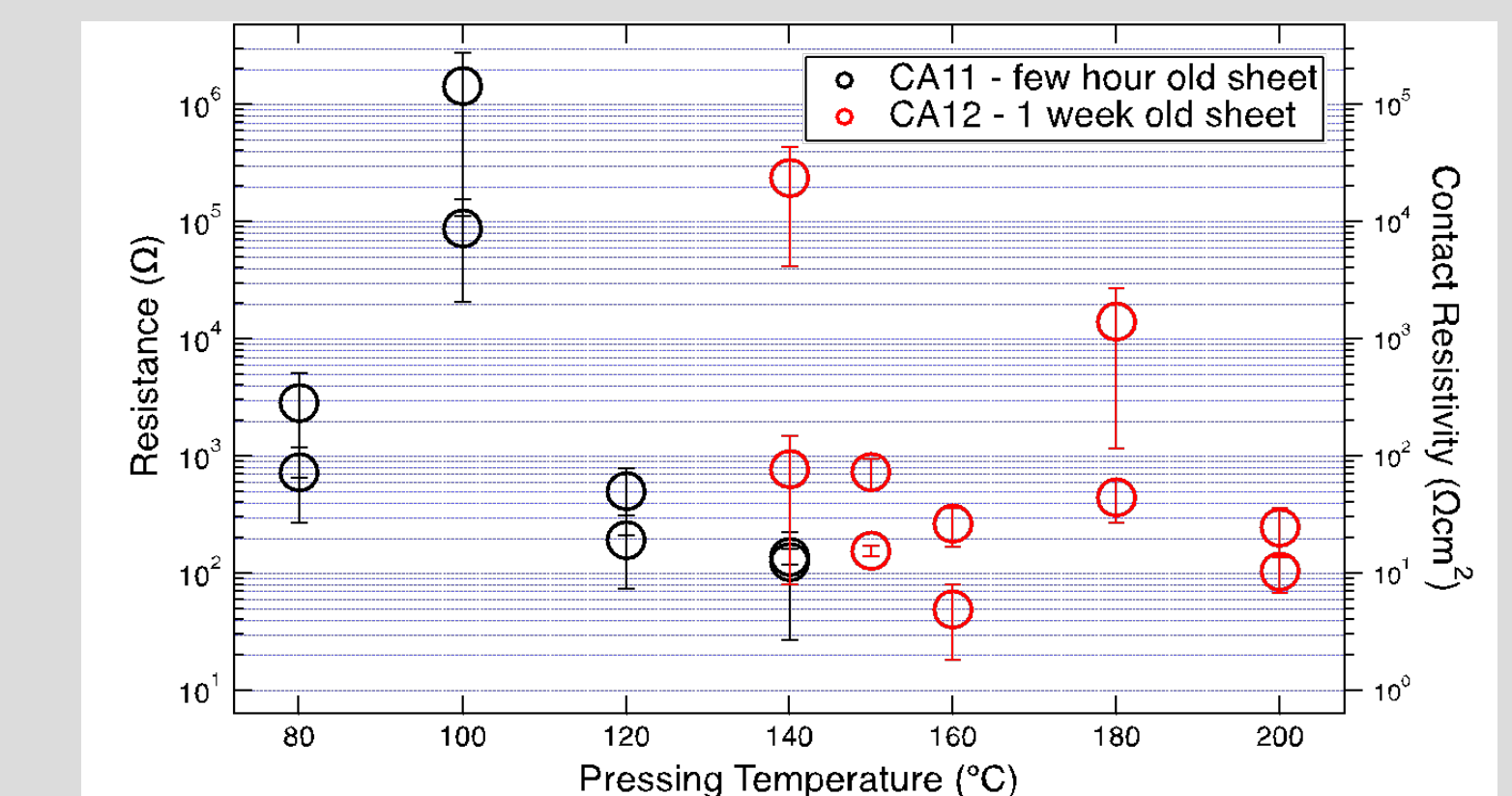
- Indium might be better since In solder is known to have 1000x lower contact resistance to Si than Ag-based conductive paint.

EVA with In Filler

- Compared AgMS and In using samples with 10wt% conductive filler, pressed at 130 psi for 20 min. (AgMS: 120°C, In: 100°C).
- Conductive particles are reflective, but no significant improvement in electrical data switching from AgMS to In.



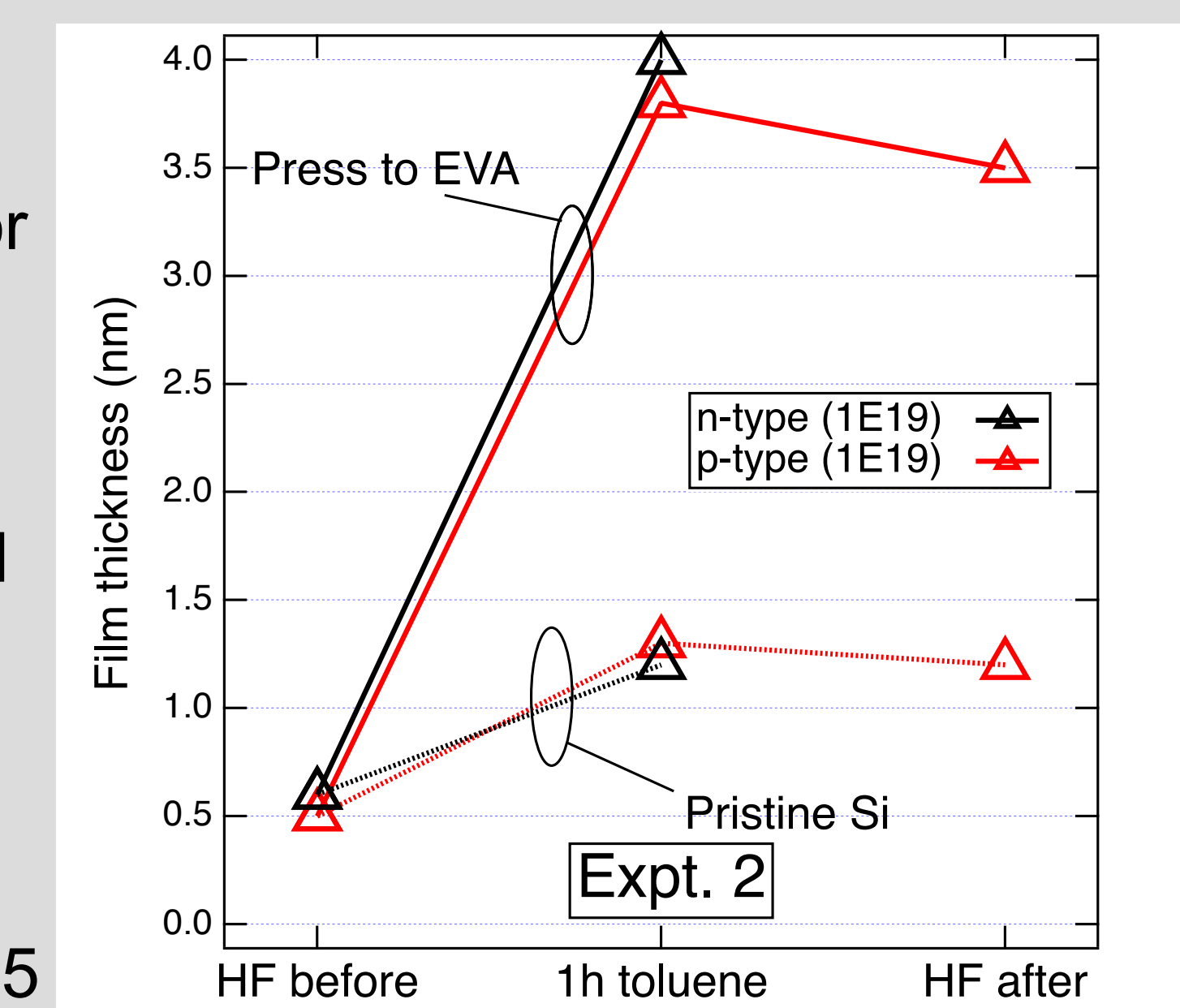
- Poor electrical data might be due to pressing In at the wrong temperature. A temperature series shows 140°C is optimal.



EVA/In temperature series shows variation and no clear trends from 120°C to 200°C

EVA Reaction with Si

- EVA might be re-oxidizing Si keeping it from making good contact.
- EVA is acidic containing O₂ and water.
- HF-etched p+ and n+ Si hot pressed to 8wt% EVA/AgMS at 120°C for 10 min. and 190 psi.
- Soaked in toluene for 1 hr. to remove CA and did ellipsometry with SiO_x model.
- Samples have 3-4 nm film compared to 1.0-1.5 for EVA-free references.



Conclusion & Outlook

- Varying temperature and pressure yields over 10 Ωcm² for CAs with AgMS and In in EVA.
- Poor contact and multiple orders of magnitude difference across samples is tentatively attributed to an interfacial film revealed with ellipsometry and to be identified by XPS spectroscopy.
- An alternative adhesive must be found that does not create a resistive interfacial film.